

Subcl

a reverse-tunneling layer over the first surface;
a first transparent ohmic contact electrode
positioned directly on the reverse-tunneling layer;
and

5 a second transparent ohmic contact electrode
positioned over the second surface.

A' ant.

10 2. (Amended) The light emitting diode of claim 1,
wherein the insulating substrate comprises sapphire,
and the first transparent ohmic contact electrode
and the second transparent ohmic contact electrode
comprise the same material.

15 3. (Amended) The light emitting diode of claim 1,
wherein the first transparent ohmic contact
electrode or the second transparent ohmic contact
electrode comprises at least one selected from a
group comprising indium tin oxide (ITO), cadmium tin
oxide (CTO), and titanium-tungsten nitride (TiWN).

20

4. (Amended) A light emitting diode comprising:

a substrate;

a semiconductor stack positioned over the
substrate;

25 a reverse-tunneling layer over the semiconductor
stack; and

an ohmic contact electrode formed directly on the
reverse-tunneling layer.

30 8. (New) The light emitting diode of claim 4, wherein
the ohmic contact electrode is a transparent ohmic
contact electrode.

*A 2
Subcl*

- 92
enclosed
9. (New) The light emitting diode of claim 8, wherein the transparent ohmic contact electrode is a non-metal transparent ohmic contact electrode.
-

5